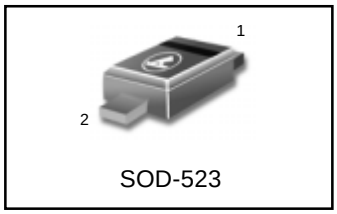
SCHOTTKY BARRIER DIODE

LRB521S-40T1G
S-LRB521S-40T1G



SOD-523

●Applictions

Low current rectification and high speed switching

●Features

Extremelysmall surface mounting type. (SOD523)

I_O=200mA guaranteed despite the size.

Low V_F.

S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

●Construction

Silicon epitaxial planar

- We declare that the material of product compliance with RoHS requirements.

Ordering Information

Device	Marking	Shipping
LRB521S-40T1G S-LRB521S-40T1G	S	3000/Tape&Reel
LRB521S-40T3G S-LRB521S-40T3G	S	10000/Tape&Reel

MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	200	mA
Peak forward surge current*	I_{FSM}	4	A
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55~+125	℃

*60Hz for 1

ELECTRICAL CHARACTERISTICS(T_A= 25°C)

Parameter	Symbol	Min.	Max.	Unit	Conditions
Forward voltage	V_F	0.16	0.30	V	I_F=10mA
Forward voltage	V_F	0.31	0.45	V	I_F=100mA
Forward voltage	V_F	0.37	0.52	V	I_F=200mA
Reverse current	I_R	–	20	μA	V_R=10V
Reverse current	I_R	–	90	μA	V_R=40V
ESD break down voltage	ESD	8	–	K V	C=100pFR=1.5K Ω forward and reverse1 time

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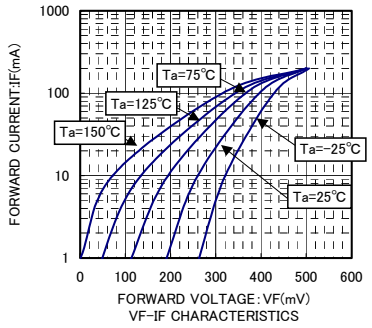
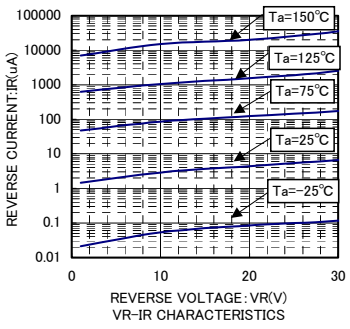
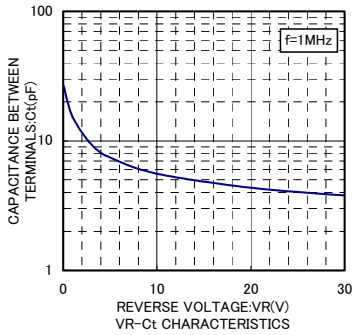
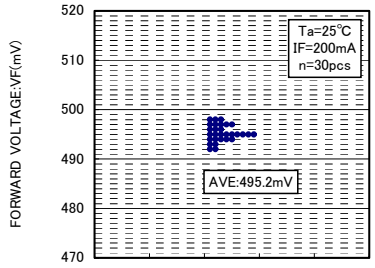
●Electrical characteristic curves

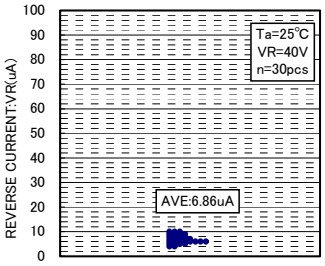




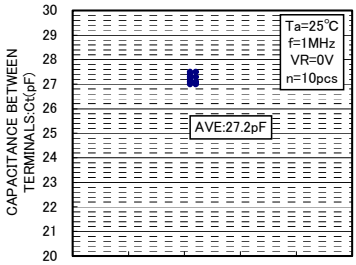




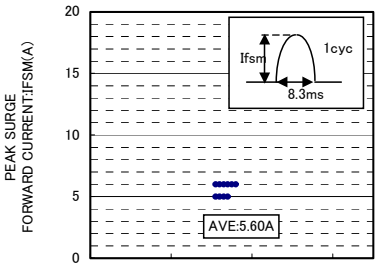
VF DISPERSION MAP



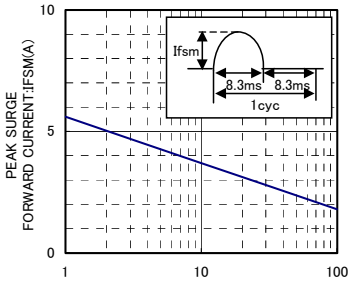
IR DISPERSION MAP

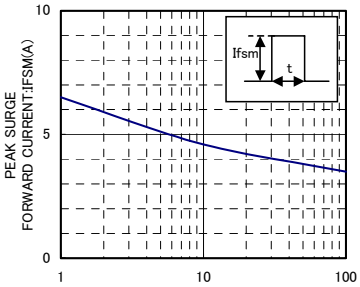


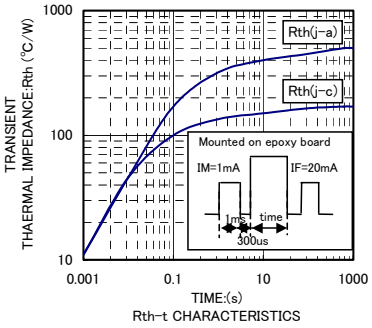
Ct DISPERSION MAP

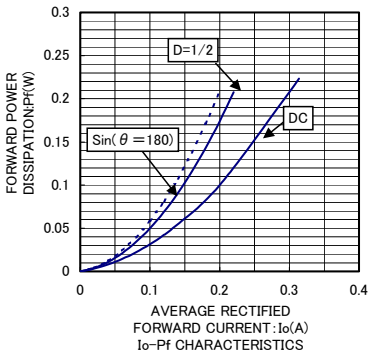


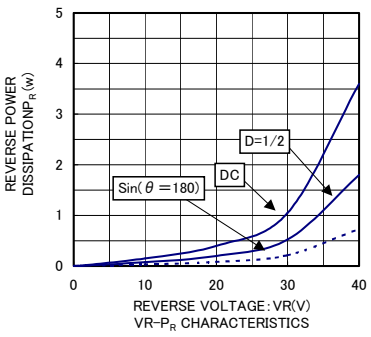
IFSM DISPERSION MAP











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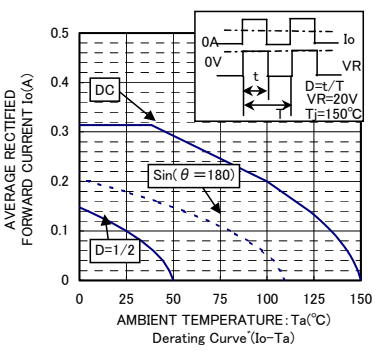
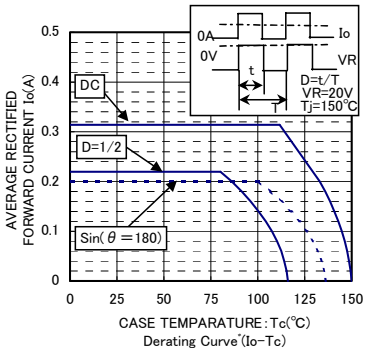
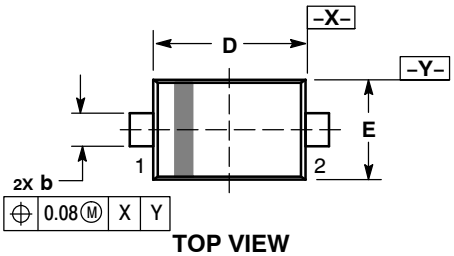


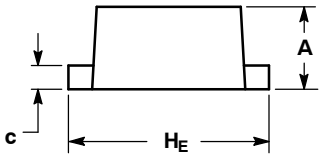


LRB521S-40T1G , S-LRB521S-40T1G

SOD−523



TOP VIEW

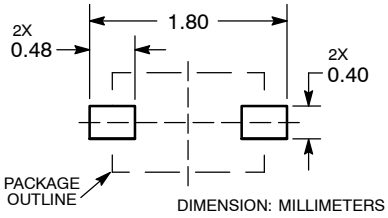


SIDE VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H_E	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSION: MILLIMETERS